

Yukari Ishikawa

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/1872892/publications.pdf>

Version: 2024-02-01

113
papers

1,242
citations

394421

19
h-index

477307

29
g-index

114
all docs

114
docs citations

114
times ranked

911
citing authors

#	ARTICLE	IF	CITATIONS
1	Correlation between dislocations and leakage current of p-n diodes on a free-standing GaN substrate. Applied Physics Letters, 2018, 112, .	3.3	142
2	SiGe-based semiconductor-on-insulator substrate created by low-energy separation-by-implanted-oxygen. Applied Physics Letters, 1998, 72, 3485-3487.	3.3	68
3	SiGe-on-insulator substrate using SiGe alloy grown Si(001). Applied Physics Letters, 1999, 75, 983-985.	3.3	50
4	Color control of white photoluminescence from carbon-incorporated silicon oxide. Journal of Applied Physics, 2008, 104, 083522.	2.5	42
5	Growth of Aluminum Nitride Films on Silicon by Electron-Cyclotron-Resonance-Assisted Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1992, 31, L1714-L1717.	1.5	38
6	Transmission Electron Microscopy Analysis of a Threading Dislocation with $\frac{c+a}{2}$ Burgers Vector in 4H-SiC. Applied Physics Express, 2012, 5, 081301.	2.4	36
7	Strong White Photoluminescence from Carbon-Incorporated Silicon Oxide Fabricated by Preferential Oxidation of Silicon in Nano-Structured Si:C Layer. Japanese Journal of Applied Physics, 2007, 46, L465-L467.	1.5	30
8	X-ray diffraction and Raman characterization of $\hat{\Gamma}^2$ -Ga ₂ O ₃ single crystal grown by edge-defined film-fed growth method. Journal of Applied Physics, 2019, 126, .	2.5	29
9	Fabrication of highly oriented Si:SiO ₂ nanoparticles using low energy oxygen ion implantation during Si molecular beam epitaxy. Applied Physics Letters, 1996, 68, 2249-2251.	3.3	28
10	Molten KOH Etching with Na ₂ O ₂ Additive for Dislocation Revelation in 4H-SiC Epilayers and Substrates. Japanese Journal of Applied Physics, 2011, 50, 075502.	1.5	27
11	Expansion of a single Shockley stacking fault in a 4H-SiC (112 \hat{A} 0) epitaxial layer caused by electron beam irradiation. Journal of Applied Physics, 2018, 123, .	2.5	27
12	Epitaxy-ready Si/SiO ₂ Bragg reflectors by multiple separation-by-implanted-oxygen. Applied Physics Letters, 1996, 69, 3881-3883.	3.3	26
13	Identification of Burgers vectors of dislocations in monoclinic $\hat{\Gamma}^2$ -Ga ₂ O ₃ via synchrotron x-ray topography. Journal of Applied Physics, 2020, 127, .	2.5	24
14	Revelation of Dislocations in $\hat{\Gamma}^2$ -Ga ₂ O ₃ Substrates Grown by Edge-Defined Film-Fed Growth. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900630.	1.8	23
15	Preparation of Thin Silicon-on-Insulator Films by Low-Energy Oxygen Ion Implantation. Japanese Journal of Applied Physics, 1991, 30, 2427-2431.	1.5	22
16	Effects of Surface Oxides of SiC on Carbon Nanotube Formation by Surface Decomposition. Japanese Journal of Applied Physics, 2003, 42, 1380-1385.	1.5	22
17	Characterization of threading dislocations in GaN (0001) substrates by photoluminescence imaging, cathodoluminescence mapping and etch pits. Journal of Crystal Growth, 2017, 468, 484-488.	1.5	22
18	Preparation of multilayered thin silicon-on-insulator structure by low-energy oxygen ion implantation. Applied Physics Letters, 1992, 61, 1543-1545.	3.3	19

#	ARTICLE	IF	CITATIONS
19	Molten KOH Etching with Na ₂ O Additive for Dislocation Revelation in 4H-SiC Epilayers and Substrates. Japanese Journal of Applied Physics, 2011, 50, 075502.	1.5	19
20	Effects of Synthesis Process on Luminescence Properties and Structure of Mesoporous Carbon-Silica Nanocomposite. Japanese Journal of Applied Physics, 2012, 51, 082402.	1.5	19
21	Observation of dislocations in $\hat{2}$ -Ga ₂ O ₃ single-crystal substrates by synchrotron X-ray topography, chemical etching, and transmission electron microscopy. Japanese Journal of Applied Physics, 2020, 59, 045502.	1.5	18
22	Slip planes in monoclinic $\hat{2}$ -Ga ₂ O ₃ revealed from its {010} face via synchrotron X-ray diffraction and X-ray topography. Japanese Journal of Applied Physics, 2020, 59, 125501.	1.5	18
23	Growth of N-Polar Aluminum Nitride on Vicinal Sapphire Substrates and Aluminum Nitride Bulk Substrates. Physica Status Solidi (B): Basic Research, 2020, 257, 1900588.	1.5	17
24	Formation mechanisms of dislocation and Si island in low-energy SIMOX. Nuclear Instruments & Methods in Physics Research B, 1994, 91, 520-524.	1.4	16
25	Influence of Annealing on the 1.5 $\hat{1}$ / ₄ m Light Emission of Er-doped ZnO Thin Films and its Crystal Quality. Journal of Materials Research, 2005, 20, 2578-2582.	2.6	15
26	Epitaxial Growth of 3C-SiC on Thin Silicon-on-Insulator Substrate by Chemical Vapor Deposition Using Alternating Gas Supply. Japanese Journal of Applied Physics, 2000, 39, L617-L619.	1.5	13
27	Correlation between etch pits formed by molten KOH+Na ₂ O ₂ etching and dislocation types in heavily doped n ⁺ -4H-SiC studied by X-ray topography. Journal of Crystal Growth, 2013, 364, 7-10.	1.5	13
28	Correlation between structural properties and nonradiative recombination behaviors of threading dislocations in freestanding GaN substrates grown by hydride vapor phase epitaxy. CrystEngComm, 2020, 22, 8299-8312.	2.6	13
29	Growth and Characterization of Nitrogen-Polar AlGa _n /AlN Heterostructure for High-Electron-Mobility Transistor. Physica Status Solidi (B): Basic Research, 2020, 257, 1900589.	1.5	13
30	Highly oriented Si nanoparticles in SiO ₂ created by Si molecular beam epitaxy with oxygen implantation. Thin Solid Films, 1997, 294, 227-230.	1.8	12
31	Preparation of Silicon-on-Insulator Substrate on Large Free-Standing Carbon Nanotube Film Formation by Surface Decomposition of SiC Film. Japanese Journal of Applied Physics, 2003, 42, 1717-1721.	1.5	12
32	Characterization of dislocations in GaN layer grown on 4-inch Si(111) with AlGa _n /AlN strained layer superlattices. Japanese Journal of Applied Physics, 2016, 55, 05FB08.	1.5	12
33	Mg diffusion and activation along threading dislocations in GaN. Applied Physics Letters, 2020, 116, .	3.3	12
34	White Light Emission from Mesoporous Carbon-Silica Nanocomposites. Japanese Journal of Applied Physics, 2011, 50, 01AF06.	1.5	12
35	Screw dislocations on $\$left\{1\bar{1}1\right\}$ pyramidal planes induced by Vickers indentation in HVPE GaN. Japanese Journal of Applied Physics, 2020, 59, 091005.	1.5	11
36	Creation of [110]-aligned Si quantum wires encompassed by SiO ₂ using low-energy separation-by-implanted-oxygen on a V-groove patterned substrate. Applied Physics Letters, 1998, 72, 2592-2594.	3.3	10

#	ARTICLE	IF	CITATIONS
37	White Light Emission from Mesoporous Carbon-Silica Nanocomposites. Japanese Journal of Applied Physics, 2011, 50, 01AF06.	1.5	10
38	Observation of dislocations and their arrays in physical vapor transport-grown AlN single-crystal substrate by synchrotron X-ray topography. Japanese Journal of Applied Physics, 2019, 58, SCCB29.	1.5	10
39	Creation of Highly Oriented Freestanding Carbon Nanotube Film by Sublimating Decomposition of Silicon Carbide Film. Japanese Journal of Applied Physics, 2000, 39, L1057-L1059.	1.5	9
40	Substrate-Polarity Dependence of AlN Single-Crystal Films Grown on 6H-SiC(0001) and (000 $\bar{1}$) by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2003, 42, 2829-2833.	1.5	9
41	Characterization of Surface Defects of Highly N-Doped 4H-SiC Substrates that Produce Dislocations in the Epitaxial Layer. Materials Science Forum, 0, 645-648, 351-354.	0.3	9
42	Dislocation Revelation in Highly Doped N-Type 4H-SiC by Molten KOH Etching with NaOH Additive. Materials Science Forum, 0, 679-680, 290-293.	0.3	9
43	Dislocation Analysis in Highly Doped n-Type 4H-SiC by Using Electron Beam Induced Current and KOH+NaOH Etching. Materials Science Forum, 0, 679-680, 294-297.	0.3	9
44	Three-Dimensional Observation of Internal Defects in a $\hat{\Gamma}^2$ -Ga ₂ O ₃ (001) Wafer Using the FIB-SEM Serial Sectioning Method. Journal of Electronic Materials, 2020, 49, 5190-5195.	2.2	9
45	White light emitting Mesoporous Carbon-Silica Nanocomposite. IOP Conference Series: Materials Science and Engineering, 2011, 18, 102019.	0.6	8
46	Observation of reaction between a-type dislocations in GaN layer grown on 4-in. Si(111) substrate with AlGa _x N strained layer superlattice after dislocation propagation. Journal of Crystal Growth, 2017, 468, 536-540.	1.5	8
47	Observation of dislocations in thick $\hat{\Gamma}^2$ -Ga ₂ O ₃ single-crystal substrates using Borrmann effect synchrotron x-ray topography. APL Materials, 2022, 10, .	5.1	8
48	Creation of Highly-Ordered Si Nanocrystal Dots Suspended in SiO ₂ by Molecular Beam Epitaxy with Low Energy Oxygen Implantation. Japanese Journal of Applied Physics, 1997, 36, 4035-4037.	1.5	7
49	Epitaxial Si/SiO ₂ low dimensional structures. Thin Solid Films, 1998, 321, 234-240.	1.8	7
50	Factors limiting the composition window for fabrication of SiGe-on-insulator substrate by low-energy oxygen implantation. Thin Solid Films, 2000, 369, 213-216.	1.8	7
51	Analysis of reaction between c+a and -c+a dislocations in GaN layer grown on 4-inch Si(111) substrate with AlGa _x N strained layer superlattice by transmission electron microscopy. AIP Advances, 2016, 6, .	1.3	7
52	Crystallinity Evaluation and Dislocation Observation for an Aluminum Nitride Single-Crystal Substrate on a Wafer Scale. Journal of Electronic Materials, 2020, 49, 5144-5153.	2.2	7
53	Size of dislocation patterns induced by Vickers indentation in hydride vapor-phase epitaxy GaN. Journal of Applied Physics, 2022, 131, .	2.5	7
54	Oxygen redistribution during low-energy oxygen implantation. Nuclear Instruments & Methods in Physics Research B, 1995, 95, 491-495.	1.4	6

#	ARTICLE	IF	CITATIONS
55	Synthesis of white light emitting mesoporous carbon-silica nanocomposite. IOP Conference Series: Materials Science and Engineering, 2011, 18, 102022.	0.6	6
56	A simultaneous observation of dislocations in 4H-SiC epilayer and n+-substrate by using electron beam induced current. Journal of Applied Physics, 2011, 109, .	2.5	6
57	Dislocation Formation in Epitaxial Film by Propagation of Shallow Dislocations on 4H-SiC Substrate. Materials Science Forum, 0, 717-720, 383-386.	0.3	6
58	White light emission from amorphous silicon oxycarbide materials. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1022-1025.	1.8	6
59	Dislocation classification of a large-area \hat{I}^2 -Ga ₂ O ₃ single crystal via contrast analysis of affine-transformed X-ray topographs. Journal of Crystal Growth, 2020, 548, 125825.	1.5	6
60	Optically detected magnetic resonance studies of donor-acceptor recombination processes in \hat{I}^2 -type GaP crystals. Journal of Applied Physics, 1989, 65, 2035-2041.	2.5	5
61	Simultaneous Si molecular beam epitaxy and high-dose ion implantation. Journal of Crystal Growth, 1995, 150, 980-983.	1.5	5
62	Nano-Order Structural Analysis of White Light-Emitting Silicon Oxide Prepared by Successive Thermal Carbonization/Oxidation of the Porous Silicon. Materials Science Forum, 2007, 561-565, 1127-1130.	0.3	5
63	Boron addition effects on aluminum nitride fabricated by radio-frequency plasma-assisted molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2486-2489.	0.8	5
64	The nature of white luminescence in SiO ₂ :C layers. Technical Physics Letters, 2009, 35, 559-562.	0.7	5
65	AFM Observation of Etch-Pit Shapes on \hat{I}^2 -Ga ₂ O ₃ (001) Surface Formed by Molten Alkali Etching. Materials Science Forum, 0, 1004, 512-518.	0.3	5
66	Generation of dislocations from scratches on GaN formed during wafer fabrication and dislocation reactions during homoepitaxial growth. Japanese Journal of Applied Physics, 2021, 60, 115501.	1.5	5
67	A synchrotron X-ray topography study of crystallographic defects in ScAlMgO ₄ single crystals. Journal of Alloys and Compounds, 2022, 896, 163025.	5.5	5
68	Mechanism of molten KOH+NaOH etching of GaN revealed by the slopes of etch pits formed at threading dislocations. Journal of Alloys and Compounds, 2022, 902, 163830.	5.5	5
69	Etch pit formation on \hat{I}^2 -Ga ₂ O ₃ by molten KOH+NaOH and hot H ₃ PO ₄ and their correlation with dislocations. Journal of Alloys and Compounds, 2022, 910, 164788.	5.5	5
70	Large-area total-thickness imaging and Burgers vector analysis of dislocations in \hat{I}^2 -Ga ₂ O ₃ using bright-field x-ray topography based on anomalous transmission. Applied Physics Letters, 2022, 121, .	3.3	5
71	Stratified suspension of highly ordered Si nanoparticles in SiO ₂ created by Si MBE with oxygen co-implantation. Journal of Crystal Growth, 1997, 175-176, 493-498.	1.5	4
72	Fabrication of [110]-aligned Si quantum wires embedded in SiO ₂ by low-energy oxygen implantation. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 304-309.	1.4	4

#	ARTICLE	IF	CITATIONS
73	SiGe-on-insulator substrate fabricated by low energy oxygen implantation. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 43-48.	1.4	4
74	Carbonization of Porous Silicon for 3C-SiC Growth. Materials Science Forum, 2007, 556-557, 167-170.	0.3	4
75	Preparation of light emitting material by thermal treatment of Rice Husks. IOP Conference Series: Materials Science and Engineering, 2011, 18, 102015.	0.6	4
76	Variation of Etch Pit Size by Screw Dislocation Tilt in 4H-SiC Wafer. Materials Science Forum, 2012, 717-720, 367-370.	0.3	4
77	Cross-sectional observation of stacking faults in 4H-SiC by KOH etching on nonpolar $\{1\bar{1}00\}$ face, cathodoluminescence imaging, and transmission electron microscopy. Japanese Journal of Applied Physics, 2014, 53, 081301.	1.5	4
78	Study of dislocations in AlN single-crystal using bright-field synchrotron x-ray topography under a multiple-beam diffraction condition. Applied Physics Letters, 2020, 117, 092102.	3.3	4
79	X-ray topography of crystallographic defects in wide-bandgap semiconductors using a high-resolution digital camera. Japanese Journal of Applied Physics, 2021, 60, 010908.	1.5	4
80	White Photoluminescence from Carbon-Incorporated Silica Fabricated from Rice Husk. Japanese Journal of Applied Physics, 2012, 51, 01AK02.	1.5	4
81	Deep ultraviolet emission from multiple quantum wells on flat N-polar AlN templates fabricated using periodical pulsed H ₂ etching. Japanese Journal of Applied Physics, 2021, 60, 125502.	1.5	4
82	Visualization of the curving of crystal planes in \hat{r}^2 -Ga ₂ O ₃ by X-ray topography. Journal of Crystal Growth, 2021, 576, 126376.	1.5	4
83	Room-Temperature Visible Photoluminescence from Single Crystal Si Quantum Well Structures. Japanese Journal of Applied Physics, 2002, 41, 5177-5180.	1.5	3
84	Growth and Characterization of AlBN Polycrystalline Thin Film by Radio-Frequency Plasma-Assisted Molecular Beam Epitaxy. Key Engineering Materials, 2006, 301, 95-98.	0.4	3
85	Elementary Screw and Mixed-Type Dislocations in 4H-SiC Characterized by X-Ray Topography Taken with Six Equivalent $11\bar{2}8$ Vectors and a Comparison to Etch Pit Evaluation. Materials Science Forum, 0, 897, 185-188.	0.3	3
86	Formation of Au and AuSi _x -Pyramids in Separation by Implanted Oxygen Wafers with Si Pillars in SiO ₂ Layer. Japanese Journal of Applied Physics, 1995, 34, L1478-L1481.	1.5	3
87	Studies of Electron-Hole Recombination Processes at Deep Levels in GaAs and GaP by Means of Transient Optical Absorption Spectroscopy. Materials Science Forum, 1991, 38-41, 1265-1270.	0.3	2
88	Formation of Au and AuSi _x -Pyramids in Separation by Implanted Oxygen Wafers with Si Pillars in SiO ₂ Layer. Japanese Journal of Applied Physics, 1995, 34, L1478.	1.5	2
89	In Situ Transmission Electron Microscopy Observation of Au-Si Interface Reaction. Japanese Journal of Applied Physics, 1996, 35, L796-L798.	1.5	2
90	White Photoluminescence from Carbon-Incorporated Silica Fabricated from Rice Husk. Japanese Journal of Applied Physics, 2012, 51, 01AK02.	1.5	2

#	ARTICLE	IF	CITATIONS
91	Anisotropic radius of curvature of crystal planes in wide-bandgap semiconductor wafers measured by X-ray diffraction. Japanese Journal of Applied Physics, 2021, 60, 128004.	1.5	2
92	Three-dimensional curving of crystal planes in wide bandgap semiconductor wafers visualized using a laboratory X-ray diffractometer. Journal of Crystal Growth, 2022, 583, 126558.	1.5	2
93	High Resolution TEM Observation of Si Nanoparticle Interfaces Fabricated by SIMOX. Journal of the Ceramic Society of Japan, 1998, 106, 1255-1258.	1.3	1
94	Structure Analyses and Electrical Properties of Er-Doped ZnO Thin Films. Key Engineering Materials, 2006, 301, 71-74.	0.4	1
95	Near-Infrared Light Emissions from Er-doped ZnO Thin Films Induced by an Electrical Field. Journal of the Ceramic Society of Japan, 2007, 115, 341-343.	1.3	1
96	Characterization of Dislocation Structures in Hexagonal SiC by Transmission Electron Microscopy. Materials Science Forum, 0, 725, 11-14.	0.3	1
97	Microscopic Structure of Stepwise Threading Dislocation in 4H-SiC Substrate. Japanese Journal of Applied Physics, 2012, 51, 041301.	1.5	1
98	Characterization of Threading Edge Dislocation in 4H-SiC by X-Ray Topography and Transmission Electron Microscopy. Materials Science Forum, 0, 778-780, 366-369.	0.3	1
99	Analysis of evolution of electron-radiation-induced defects in white-luminescent, carbonized, mesoporous silica nanocomposite using transmission electron microscopy/cathodoluminescence. Nuclear Instruments & Methods in Physics Research B, 2019, 439, 22-33.	1.4	1
100	Microscopic Structure of Stepwise Threading Dislocation in 4H-SiC Substrate. Japanese Journal of Applied Physics, 2012, 51, 041301.	1.5	1
101	Identification of fine structures at the surface of epi-ready GaN wafer observed by confocal differential interference contrast microscopy. Japanese Journal of Applied Physics, 2020, 59, 100907.	1.5	1
102	Crystallinity of AlN Film Deposited by Reactive Sputtering Method. Journal of the Ceramic Society of Japan, 1994, 102, 1079-1081.	1.3	0
103	Preparation of Multilayered Thin Silicon-on-Insulator Structure.. Hyomen Gijutsu/Journal of the Surface Finishing Society of Japan, 1995, 46, 688-691.	0.2	0
104	Luminescent Characteristics of Undoped and Er-Doped ZnO Thin Films. Key Engineering Materials, 2006, 301, 189-192.	0.4	0
105	Near-Infrared Light Emission from of Er-Doped ZnO Thin Film in Micropits Processed on Si Substrate. Key Engineering Materials, 2006, 320, 113-116.	0.4	0
106	Electron Beam Induced Current Observation of Dislocations in 4H-SiC Introduced by Mechanical Polishing. Materials Science Forum, 0, 725, 23-26.	0.3	0
107	Characterization of Damage Induced by Electric Discharge Machining and Wiresawing with Loose Abrasive at Subsurface of SiC Crystal. Materials Science Forum, 2014, 778-780, 362-365.	0.3	0
108	Invited: Analysis and Detection of Dislocations in GaN. , 2019, , .		0

#	ARTICLE	IF	CITATIONS
109	Preparation of crystalline SiC coating from Si and C powder mixture using laser sublimation technique. Journal of the Ceramic Society of Japan, 2021, 129, 310-314.	1.1	0
110	Observation of Dopant Concentration in GaN Semiconductor by High Sensitivity Electron Holography. Materia Japan, 2019, 58, 103-103.	0.1	0
111	Dislocation structure around Vickers indentation on GaN. The Proceedings of Mechanical Engineering Congress Japan, 2020, 2020, S16307.	0.0	0
112	Achievement of SiGe-on-Insulator Technology. , 2005, , 65-75.		0
113	Observation of threading dislocations with a c+m type Burgers vector in HVPE GaN substrates using multi-photon excitation photoluminescence and TEM. Journal of Crystal Growth, 2022, , 126748.	1.5	0